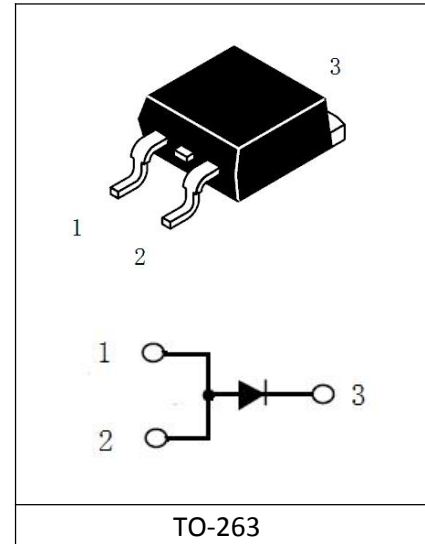


## SCHOTTKY RECTIFIERS

### Features:

- Low power loss,high efficiency
- High surge capacity
- High ESD capacity : **HBM,3B (>8000V)**
- For use in low voltage,high frequency inverters, free wheeling,and polarity protection applications
- Metal silicon junction,majority carrier conduction
- Guard ring for over voltage protection



### Absolute Maximum Ratings( $T_c=25^\circ\text{C}$ ):

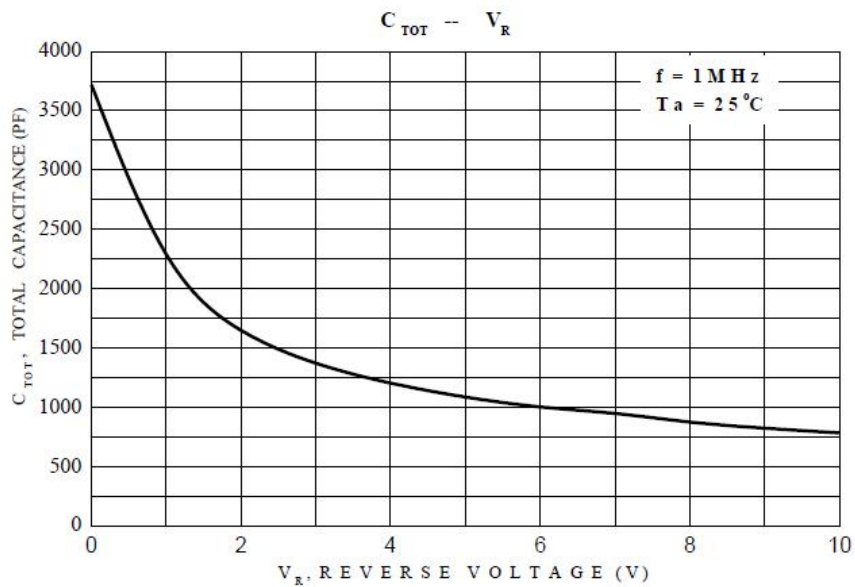
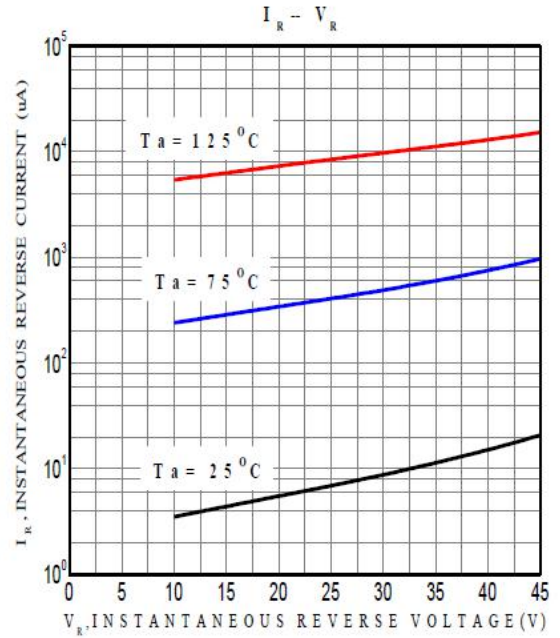
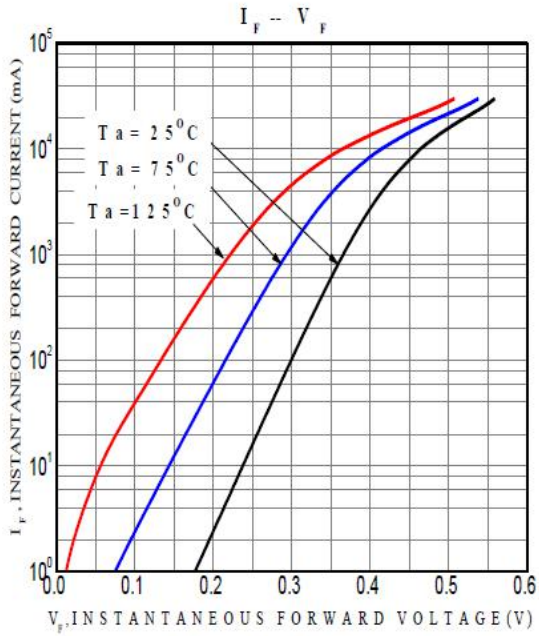
Characteristics	Symbol	Rating	Unit
Maximum Repetitive Reverse Voltage	$V_{RRM}$	45	V
Average Rectified Forward Current	$I_{F(AV)}$	30	A
Non-repetitive Peak Forward Surge Current 8.3ms Single Half-Sine-Wave	$I_{FSM}$	450	A
Collector power dissipation $T_a=25^\circ\text{C}$	$P_{tot}$	3.0	W
Junction temperature	$T_j$	175	$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-55~175	$^\circ\text{C}$

### Electrical Characteristics( $T_c=25^\circ\text{C}$ ) :

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F=30\text{A}; T_c=25^\circ\text{C}$		0.56	0.60	V
Reverse Current	$I_R$	$V_R=45\text{V}; T_c=25^\circ\text{C}$ $V_R=45\text{V}; T_c=125^\circ\text{C}$		0.02	0.12 15.0	mA
Peak Repetitive Reverse Surge Current	$I_{RRM}$	2.0 us Pulsu Width , $f=1.0\text{KHZ}$ $T_J<175^\circ\text{C}$			1.5	A

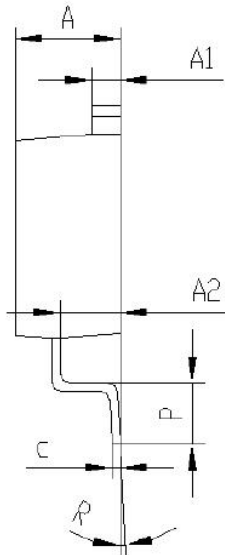
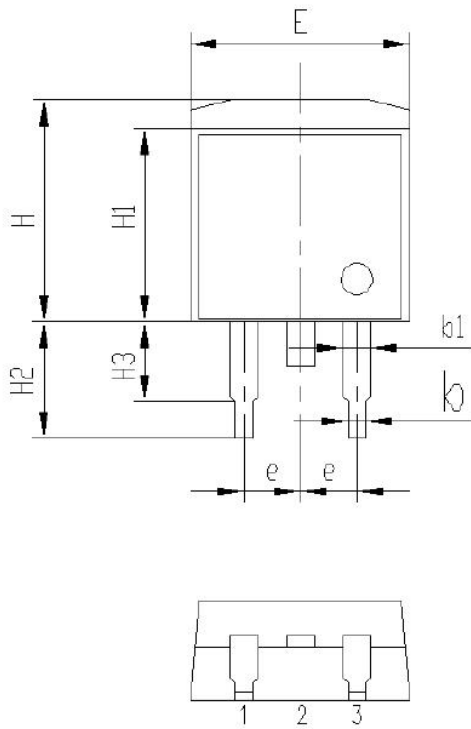
Symbol	Paramter	Typ	Units
$R_{\theta JA}$	Junction-to-Ambient	50	$^\circ\text{C}/\text{W}$

## TYPICAL CHARACTERISTICS



## Package Information

### TO-263 PACKAGE



	単位: mm		
	MIN	NOM	MAX
A	4.5	4.7	4.9
A1	1.17	1.27	1.37
A2	2.4	2.6	2.8
b	0.6	0.8	1.0
b1	0.95	1.15	1.35
c	0.26	0.38	0.5
e	2.34	2.54	2.74
E	9.7	9.9	10.1
H	9.8	10	10.2
H1	8.5	8.7	8.9
H2	5.05	5.25	5.45
H3	3.6	3.8	4
R	0	3°	6°
P	2.55	2.75	2.95